

FIG.1

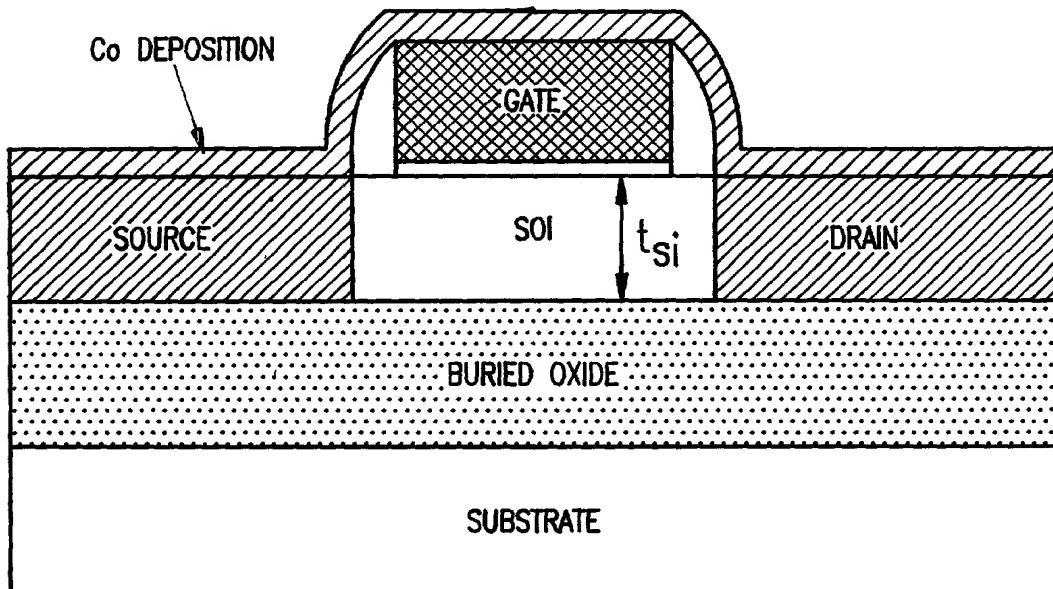


FIG.2

FORM Co_2Si BY LOW TEMPERATURE ANNEAL

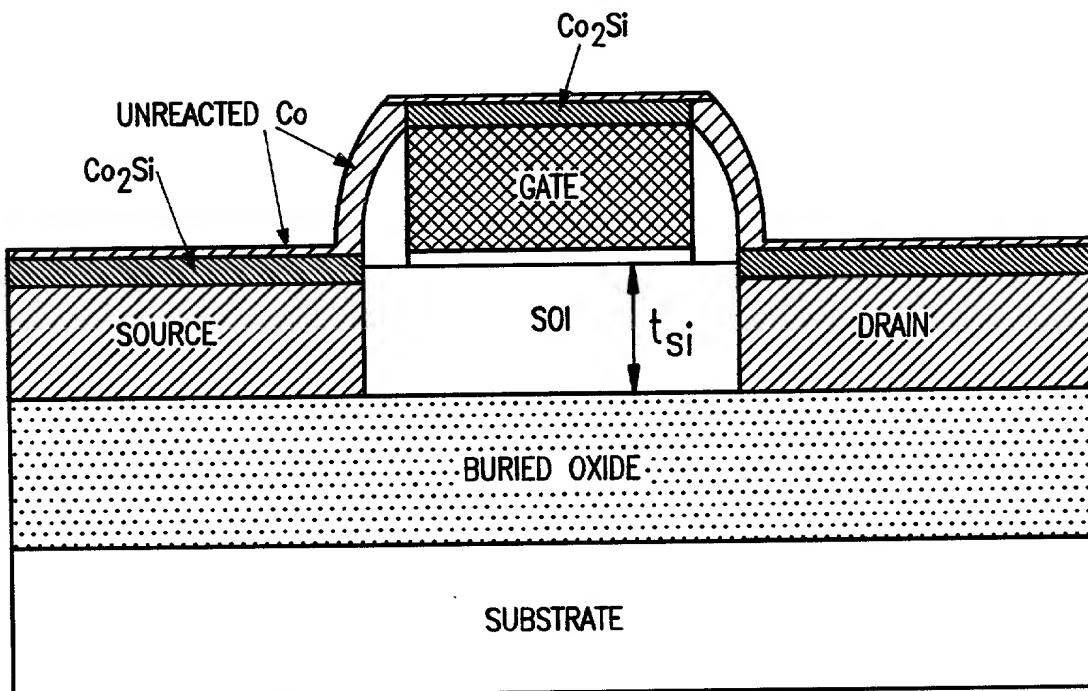


FIG.3

DEPOSITE $\alpha\text{-Si}$

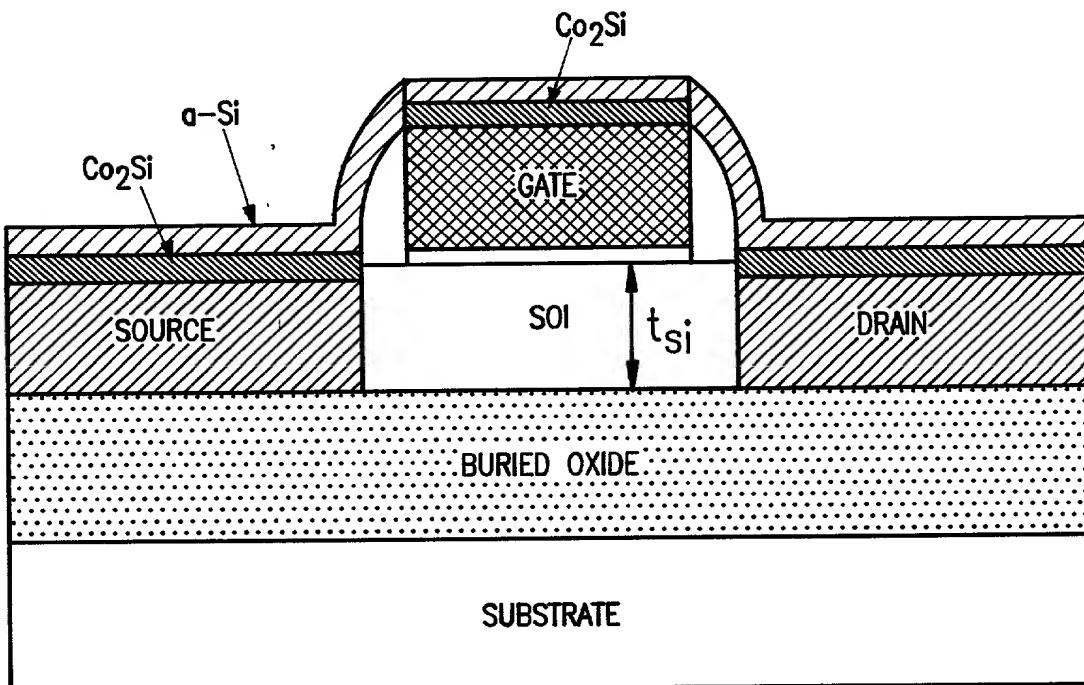


FIG.4

ANNEAL TO FORM CoSi_2

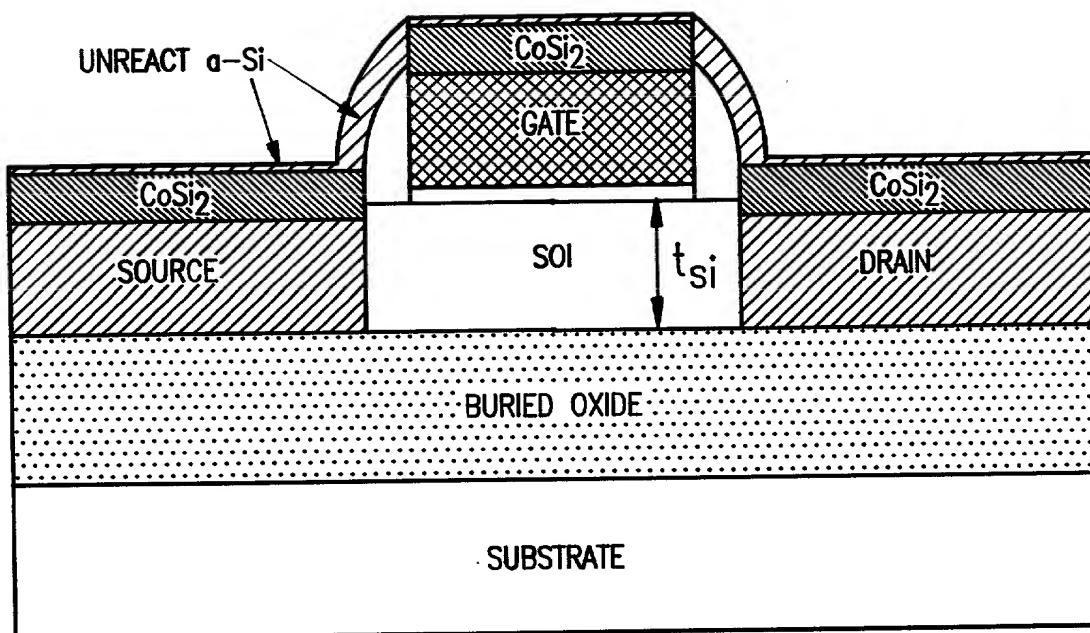


FIG.5

ETCH UNREACTED $\alpha\text{-Si}$

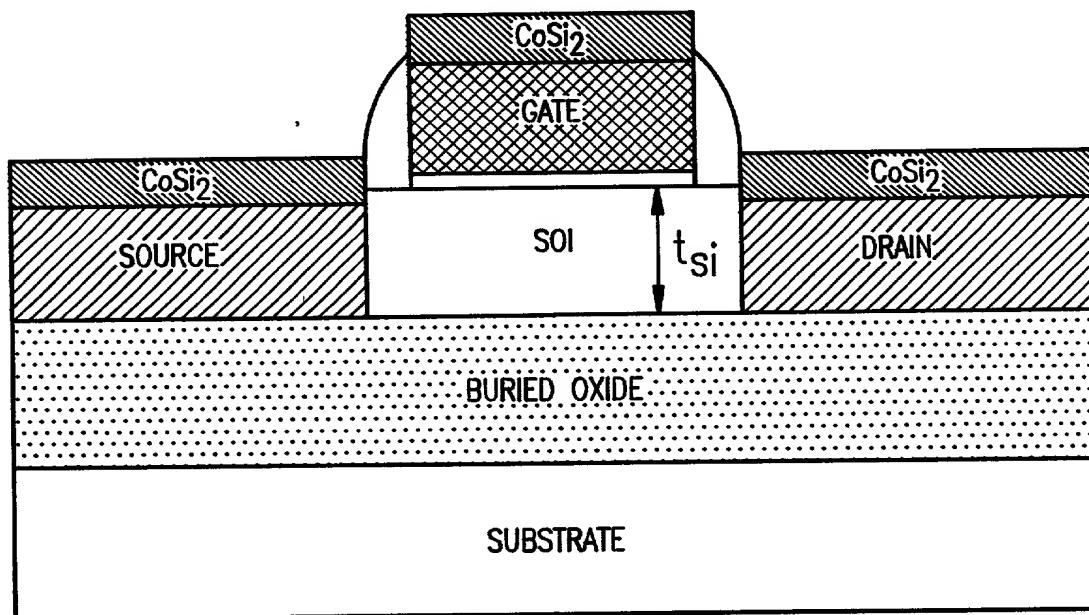


FIG.6

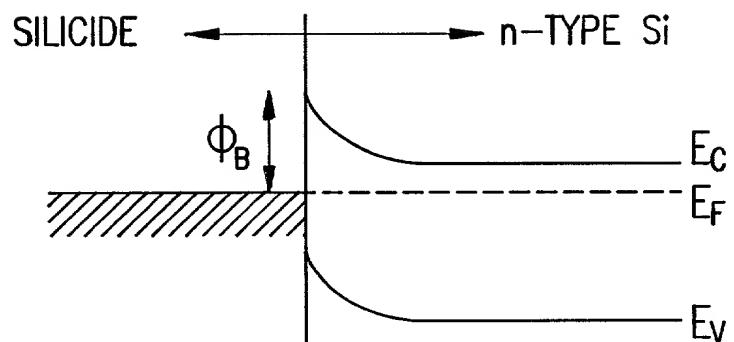


FIG. 7A

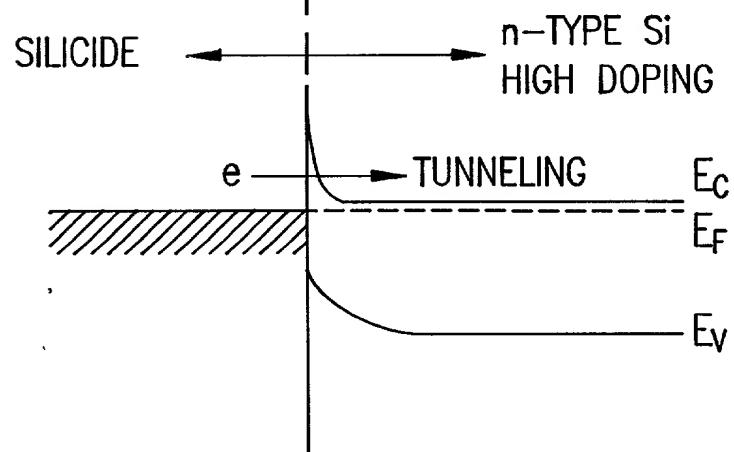
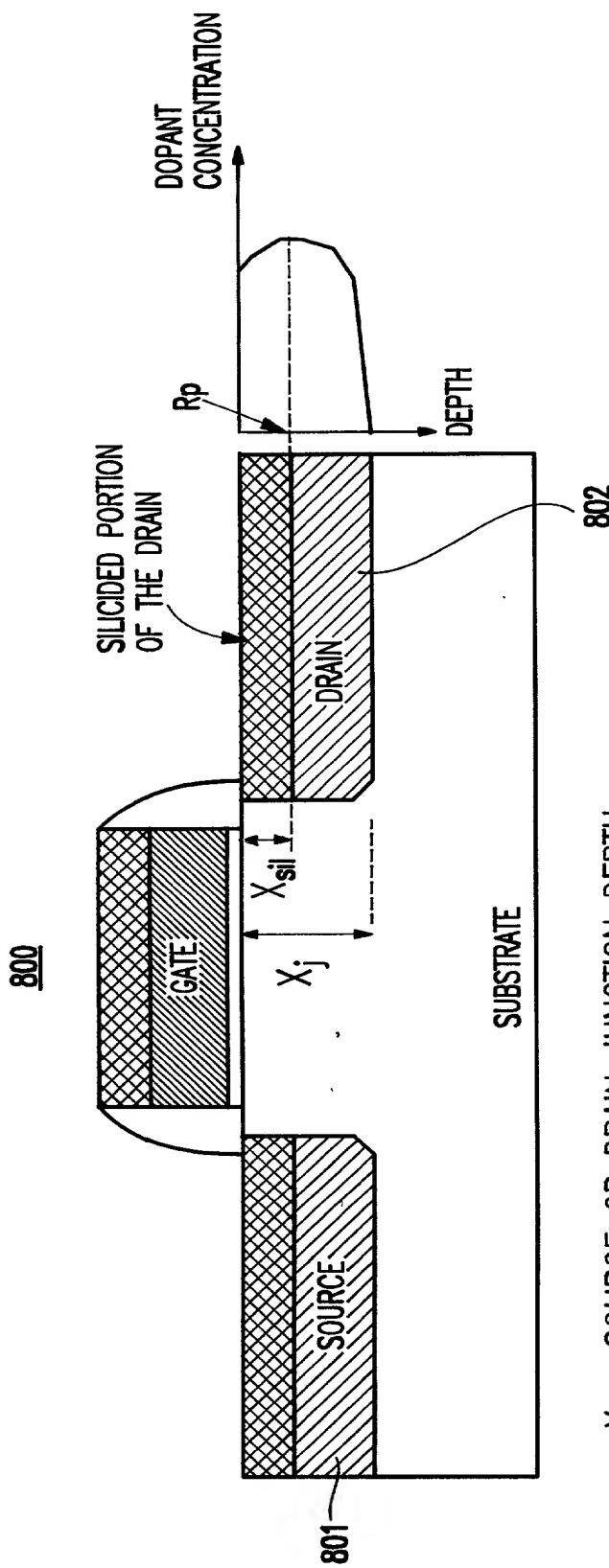


FIG. 7B



X_j = SOURCE OR DRAIN JUNCTION DEPTH

X_{sil} = SILICIDE JUNCTION DEPTH

R_p = PEAK DOPANT CONCENTRATION

REQUIREMENTS:

1. $X_j > X_{sil}$
2. X_{sil} ROUGHLY EQUALS R_p

FIG.8

